

ISC Silicon PNP Power Transistor

2SA715

DESCRIPTION

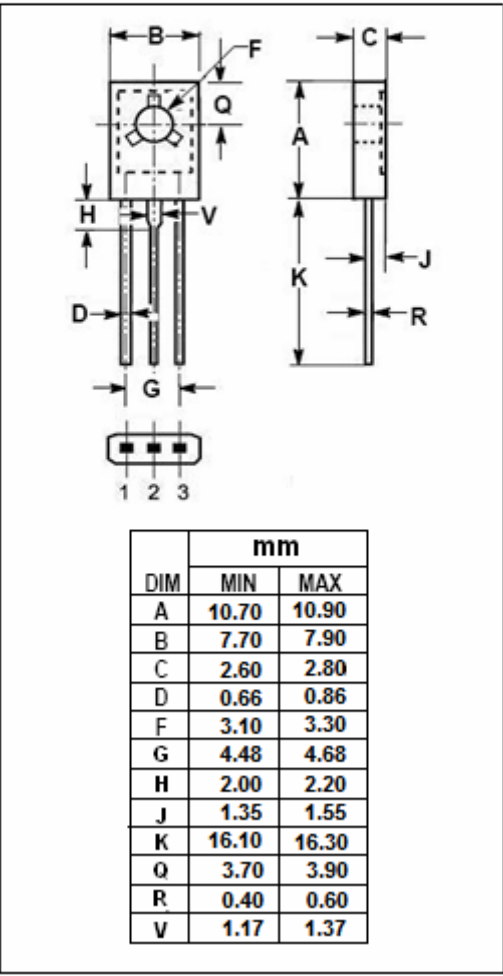
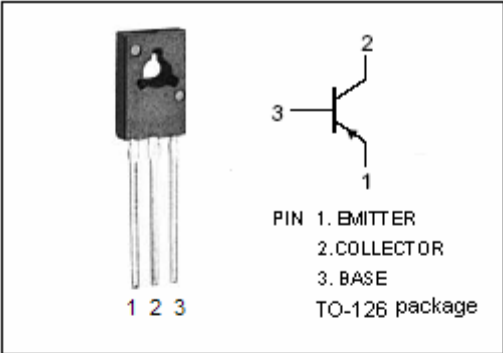
- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = -35V$ (Min)
- Complement to Type 2SC1162

APPLICATIONS

- Designed for use in low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-35	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-2.5	A
I_{CM}	Collector Current-Peak	-3.0	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}C$	0.75	W
	Total Power Dissipation @ $T_C=25^{\circ}C$	10	
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon PNP Power Transistor**2SA715****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA; I _E = 0	-35			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA; R _{BE} = ∞	-35			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA; I _C = 0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A			-1.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -1.5A ; V _{CE} = -2V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -35V; I _E = 0			-20	μ A
h _{FE-1}	DC Current Gain	I _C = -0.5A ; V _{CE} = -2V	60		320	
h _{FE-2}	DC Current Gain	I _C = -1.5A ; V _{CE} = -2V	20			
f _T	Current-Gain—Bandwidth Product	I _C = -0.2A ; V _{CE} = -2V		160		MHz

◆ h_{FE-1} Classifications

B	C	D
60-120	100-200	160-320